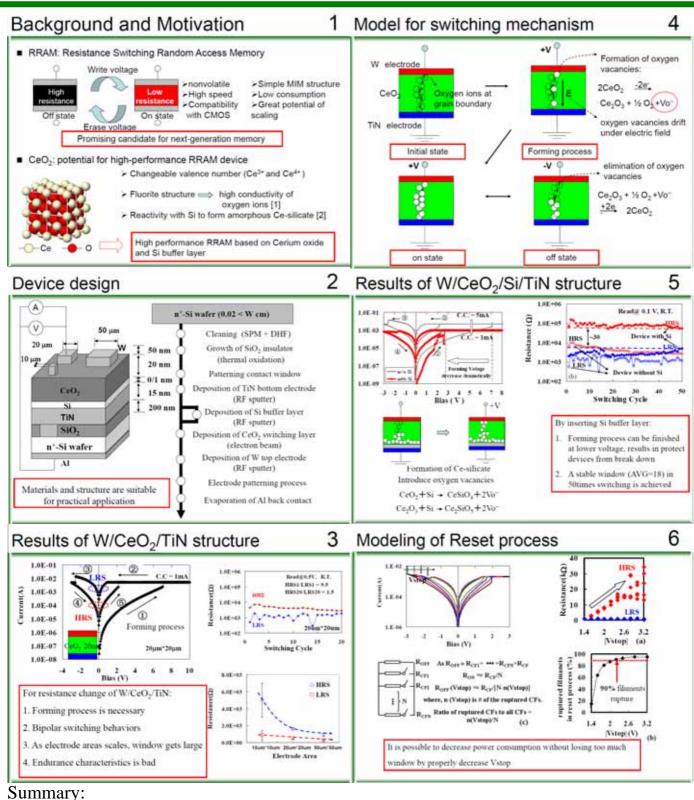
Feasibility study of Ce oxide for resistive RAM application

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- 1. The resistive switching behaviors of CeO_2 based ReRAM have been confirmed.
- 2. Si buffer layer is able to improve CeO_2 based ReRAM device by forming Ce-silicate at interface.
- 3. A guideline for reset process control of the $W/CeO_2/Si/TiN$ device is provided..